Attorney Docket No. OKUDP0176US					
IN THE UNITED STATES PATENT AND TRADEMARK OFFICE (IDO/EO/US)					
In re national phase of:	(23,23,23)				
Applicant(s):	Toshitaka SHIMAMOTO et al.				
International Application No.:	PCT/JP2005/020927				
International Filing Date:	15 November 2005				
Priority Date Claimed:	22 November 2004				
Title of Invention:	NITRIDE-BASED SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME				
INFO	RMATION DISCLOSURE STATEMENT				
Mail Stop PCT Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450					
Sir:					
the patents, pending applications, publ each listed document is enclosed exce	8, and in compliance with 37 C.F.R. 1.58, the Office's attention is directed to leations and other information listed on the attached PTC-1449. A copy of pt for: (a) pending applications or (b) those previously cited or submitted to) upon which this application relies for an earlier filling date under 35 U.S.C.				
Serial No.: Filing Date:					
Applicant(s) believe(s) the same may of	or other information for which a date is not given on the attached PTO-1449, qualify as "prior" art to this application and should be treated accordingly, that to contest the prior art status of any document, publication or				
Regarding each listed document the accompanies this Statement as indicat the document is set forth in the following	at is not in the English language, an English-language translation ed on the attached PTO-1449 or a concise explanation of the relevance of ng document(s):				
	guage version of a search report indicating the degree of relevance found ich document being submitted from the search report.				
(b) Attachment entitled "Con-	cise Explanation of Relevance of Non-English Language Documents".				
3. Pursuant to 37 C.F.R. 1.97(b) this Statement is being filed (one must be checked):					
(a) X Within 3 months of the fili	ing date, date of entry into the National Stage, or filing date of CPA.				
mailing date of a first Offi absence thereof, the Office	f a first Office Action on the ments. If this Statement is not filed before the ce Action on the ments, the required certification is given below or, in the ce is authorized to charge the required fee set forth in 37 C.F.R. 1.17(p) to 1988 for consideration of this Statement.				

Before the mailing date of a first Office Action on the ments after a first or second submission after final rejection under 37 C.F.R. 1.129(a).

		fter the period set forth in 37 C.F.R. 1.97(b) but before the mailing date of either a final action or a plice of allowance.
	(1)	The required certification is given below, \underline{or}
	(2)	Enclosed is a check covering the fee set forth in 37 C.F.R. 1.17(p) for consideration of this Statement, or
	(3)	Charge the fee set forth in 37 C.F.R. 1.17(p) to Deposit Account No. 18-0988
	fe fe	fter the mailing date of either a final action or a notice of allowance, but before payment of the issue e. Petition hereby is made for consideration of this Statement and the required certification is dicated below.
	(1)	Enclosed is a check covering the fee set forth in 37 C.F.R. 1.17(p), or
	(2)	Charge the fee set forth in 37 C.F.R. 1.17(p) to Deposit Account No. 18-0988.
4.	Certification	(if applicable)
	ci	he undersigned hereby certifies that each item of information contained in this Statement was first ted in any communication from a foreign patent office in a counterpart foreign application not more an 3 months prior to the filing of this Statement.
	a uı	he undersigned hereby certifies that no item of information contained in this Statement was cited in communication from a foreign patent office in a counterpart foreign application or, to the ddersigned's knowledge after making reasonable inquiry, was known to any individual designated in 7 C.F.R. 1.56(c) more than 3 months prior to the filing of this Statement.
	The Commi count No. 18	ssioner is hereby authorized to charge any additional fees or credit any overpayment to Deposit L-0988.
		Respectfully Submitted,
		RENNER, OTTO, BOISSELLE & SKLAR, LLP
Cle	21 Euclid Av veland, Ohi 6) 621-1113	
		CERTIFICATE OF MAILING, FACSIMILE OR ELECTRONIC TRANSMISSION
11		that this paper (along with any paper referred to as being attached or enclosed) is sited with the United States Postal Service with sufficient postage for first class mail in an envelope

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/Mark D. Saralino/ Mark D. Saralino

addressed to the Commissioner for Patents address below. X being transmitted via the USPTO Electronic Filing System.

July 31, 2006 Date

Form PTO-1449 (Modified)	Atty Docket No.	Serial No.	
LIST OF PATENTS AND PUBLICATIONS	OKUDP0176US	Unknown	
FOR APPLICANT'S	Applicant:		
INFORMATION DISCLOSURE STATEMENT	Toshitaka SHIMAMOTO et al.		
(Use several sheets if necessary)	Filing Date	Group	
(oso severa should it recessary)	July 31, 2006	Not Yet Assigned	

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date MM/YYYY	Name	Class	Sub- class	Filing Date if Appropriate
/B.F./	2003/0141512 (corresponds to JP 2003-234505)	July 2003	Bruderl et al.			
/B.F./	2003/0143771 (corresponds to JP 2002-009004)	July 2003	Kidoguchi et al.			
/B.F./	2001-0003019 (corresponds JP 2001-158698)	June 2001	Morita			
/B.F./	6,252,261 (corresponds to JP 2003-300800)	June 2001	Usui et al.			
/B.F./	6,836,498 (corresponds to JP 2002-076518)	December 2004	Takeya et al.			

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Sub- class	Translation
IIIIda		MM/YYYY				Yes No
/B.F./	2003-234505	August 2003	JP			Abstract
/B.F./	2002-009004	January 2002	JP			Abstract
/B.F./	2001-158698	June 2001	JP			Abstract
/B.F./	2003-300800	October 2003	JP			Abstract
/B.F./	2002-076518	March 2002	JP			Abstract
/B.F./	2003-086905	March 2003	JP			Abstract
/B.F./	2003-158295	May 2003	JP			Abstract
/B.F./	2001-308464	November 2001	JP			Abstract
/B.F./	2002-237656	August 2002	JP			Abstract

OTHER ART

Examiner Initial	Author, Title, Date, Perlinent Pages, etc.
/B.F./	International Search Report for corresponding Application No. PCT/JP2005/020927 mailed January 26, 2006.
/B.F./	Nagahama et al.; "High-Power and Long-Lifetime InGaN Multi-Quantum-Well Laser Diodes Grown on Low-Dislocation-Density GaN Substrates", Japanese Journal of Applied Physics Vol. 39, pages L647-650, 2000. (Cited in [0013] on page 6 of the description).
/B.F./	International Searching Authority's Written Opinion with partial English translation.

EXAMINER	/Brandon Fox/	DATE CONSIDERED 06/30/2009		
EXITING INC. Included the second state of the				

EXAMINER initial if reference considered, whether or not citation is in conformance with we-bird output copy of this form with next communication to applicant.

The identification of any reference is not increased in the interest and in the interest and in the interest and in the interest and interest